

Patrick Fiorenza

List of Publications by Year in descending order

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159
papers

3,048
citations

218381

26
h-index

214527

47
g-index

163
all docs

163
docs citations

163
times ranked

2603
citing authors

#	ARTICLE	IF	CITATIONS
1	Emerging trends in wide band gap semiconductors (SiC and GaN) technology for power devices. <i>Microelectronic Engineering</i> , 2018, 187-188, 66-77.	1.1	329
2	An Overview of Normally-Off GaN-Based High Electron Mobility Transistors. <i>Materials</i> , 2019, 12, 1599.	1.3	178
3	Recent advances on dielectrics technology for SiC and GaN power devices. <i>Applied Surface Science</i> , 2014, 301, 9-18.	3.1	130
4	Challenges for energy efficient wide band gap semiconductor power devices. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2014, 211, 2063-2071.	0.8	107
5	Non-stoichiometry in $\text{CaCu}_3\text{Ti}_4\text{O}_{12}$ (CCTO) ceramics. <i>RSC Advances</i> , 2013, 3, 14580.	1.7	98
6	Characterization of SiO ₂ /4H-SiC Interfaces in 4H-SiC MOSFETs: A Review. <i>Energies</i> , 2019, 12, 2310.	1.6	84
7	SiO ₂ /4H-SiC interface doping during post-deposition-annealing of the oxide in N ₂ O or POCl ₃ . <i>Applied Physics Letters</i> , 2013, 103, .	1.5	70
8	Silica-Added, Composite Poly(vinyl alcohol) Membranes for Fuel Cell Application. <i>Journal of the Electrochemical Society</i> , 2005, 152, A2400.	1.3	65
9	Limiting mechanism of inversion channel mobility in Al-implanted lateral 4H-SiC metal-oxide semiconductor field-effect transistors. <i>Applied Physics Letters</i> , 2011, 99, .	1.5	58
10	Critical issues for interfaces to p-type SiC and GaN in power devices. <i>Applied Surface Science</i> , 2012, 258, 8324-8333.	3.1	57
11	Correlating macroscopic and nanoscale electrical modifications of SiO ₂ /4H-SiC interfaces upon post-oxidation-annealing in N ₂ O and POCl ₃ . <i>Applied Physics Letters</i> , 2012, 101, .	1.5	52
12	Fowler-Nordheim tunneling at SiO ₂ /4H-SiC interfaces in metal-oxide-semiconductor field effect transistors. <i>Applied Physics Letters</i> , 2014, 105, .	1.5	49
13	Localized electrical characterization of the giant permittivity effect in CaCu ₃ Ti ₄ O ₁₂ ceramics. <i>Applied Physics Letters</i> , 2008, 92, .	1.5	48
14	Interface Electrical Properties of Al ₂ O ₃ Thin Films on Graphene Obtained by Atomic Layer Deposition with an in Situ Seedlike Layer. <i>ACS Applied Materials & Interfaces</i> , 2017, 9, 7761-7771.	4.0	44
15	Conductive atomic force microscopy studies of thin SiO ₂ layer degradation. <i>Applied Physics Letters</i> , 2006, 88, 222104.	1.5	43
16	Epitaxial NiO gate dielectric on AlGaN/GaN heterostructures. <i>Applied Physics Letters</i> , 2012, 100, 063511.	1.5	42
17	Negative charge trapping effects in Al ₂ O ₃ films grown by atomic layer deposition onto thermally oxidized 4H-SiC. <i>AIP Advances</i> , 2016, 6, .	0.6	42
18	Channel Mobility in GaN Hybrid MOS-HEMT Using SiO ₂ as Gate Insulator. <i>IEEE Transactions on Electron Devices</i> , 2017, 64, 2893-2899.	1.6	38

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19	Poole-Frenkel emission in epitaxial nickel oxide on AlGaIn/GaN heterostructures. Applied Physics Letters, 2012, 101, .	1.5	35
20	Comparative study of gate oxide in 4H-SiC lateral MOSFETs subjected to post-deposition-annealing in N ₂ O and POCl ₃ . Applied Physics A: Materials Science and Processing, 2014, 115, 333-339.	1.1	35
21	Slow and fast traps in metal-oxide-semiconductor capacitors fabricated on recessed AlGaIn/GaN heterostructures. Applied Physics Letters, 2015, 106, .	1.5	34
22	Calcium Copper Titanate Thin Film Growth: Tailoring of the Operational Conditions through Nanocharacterization and Substrate Nature Effects. Journal of Physical Chemistry B, 2006, 110, 17460-17467.	1.2	33
23	Breakdown kinetics of Pr ₂ O ₃ films by conductive-atomic force microscopy. Applied Physics Letters, 2005, 87, 231913.	1.5	32
24	Reliability of thermally oxidized SiO ₂ /4H-SiC by conductive atomic force microscopy. Applied Physics Letters, 2006, 88, 212112.	1.5	31
25	Influence of the surface morphology on the channel mobility of lateral implanted 4H-SiC(0001) metal-oxide-semiconductor field-effect transistors. Journal of Applied Physics, 2012, 112, .	1.1	31
26	Near interface traps in SiO ₂ /4H-SiC metal-oxide-semiconductor field effect transistors monitored by temperature dependent gate current transient measurements. Applied Physics Letters, 2016, 109, .	1.5	31
27	Selective Doping in Silicon Carbide Power Devices. Materials, 2021, 14, 3923.	1.3	31
28	Defect formation and evolution in the step-flow growth of silicon carbide: A Monte Carlo study. Journal of Crystal Growth, 2008, 310, 971-975.	0.7	29
29	Metal Organic Chemical Vapor Deposition of nickel oxide thin films for wide band gap device technology. Thin Solid Films, 2014, 563, 50-55.	0.8	29
30	Micro- and nanoscale electrical characterization of large-area graphene transferred to functional substrates. Beilstein Journal of Nanotechnology, 2013, 4, 234-242.	1.5	28
31	Direct imaging of the core-shell effect in positive temperature coefficient of resistance-BaTiO ₃ ceramics. Applied Physics Letters, 2009, 95, .	1.5	27
32	Temperature-dependent Fowler-Nordheim electron barrier height in SiO ₂ /4H-SiC MOS capacitors. Materials Science in Semiconductor Processing, 2018, 78, 38-42.	1.9	27
33	Conduction Mechanisms at Interface of AlN/SiN Dielectric Stacks with AlGaIn/GaN Heterostructures for Normally-off High Electron Mobility Transistors: Correlating Device Behavior with Nanoscale Interfaces Properties. ACS Applied Materials & Interfaces, 2017, 9, 35383-35390.	4.0	26
34	Effect of high temperature annealing (>1650°C) on the morphological and electrical properties of p-type implanted 4H-SiC layers. Materials Science in Semiconductor Processing, 2019, 93, 274-279.	1.9	26
35	From micro- to nanotransport properties in Pr ₂ O ₃ -based thin layers. Journal of Applied Physics, 2005, 98, 044312.	1.1	25
36	Perovskite CaCu ₃ Ti ₄ O ₁₂ thin films for capacitive applications: From the growth to the nanoscopic imaging of the permittivity. Journal of Applied Physics, 2009, 105, 061634.	1.1	25

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37	Impact of Stacking Faults and Domain Boundaries on the Electronic Transport in Cubic Silicon Carbide Probed by Conductive Atomic Force Microscopy. <i>Advanced Electronic Materials</i> , 2020, 6, 1901171.	2.6	25
38	Preferential oxidation of stacking faults in epitaxial off-axis (111) 3C-SiC films. <i>Applied Physics Letters</i> , 2009, 95, 111905.	1.5	24
39	Experimental characterization of proteins immobilized on Si-based materials. <i>Microelectronic Engineering</i> , 2007, 84, 468-473.	1.1	23
40	High capacitance density by CaCu ₃ Ti ₄ O ₁₂ thin films. <i>Journal of Applied Physics</i> , 2010, 108, .	1.1	23
41	Probing the uniformity of hydrogen intercalation in quasi-free-standing epitaxial graphene on SiC by micro-Raman mapping and conductive atomic force microscopy. <i>Nanotechnology</i> , 2019, 30, 284003.	1.3	23
42	Nanoscale imaging of permittivity in giant- ϵ CaCu ₃ Ti ₄ O ₁₂ grains. <i>Journal of Applied Physics</i> , 2007, 102, .	1.1	22
43	Chemical stability of CaCu ₃ Ti ₄ O ₁₂ thin films grown by MOCVD on different substrates. <i>Thin Solid Films</i> , 2007, 515, 6470-6473.	0.8	22
44	Carbonization and transition layer effects on 3C-SiC film residual stress. <i>Journal of Crystal Growth</i> , 2017, 473, 11-19.	0.7	22
45	Electron trapping at SiO ₂ /4H-SiC interface probed by transient capacitance measurements and atomic resolution chemical analysis. <i>Nanotechnology</i> , 2018, 29, 395702.	1.3	22
46	Nanoscale electrical probing of heterogeneous ceramics: the case of giant permittivity calcium copper titanate (CaCu ₃ Ti ₄ O ₁₂). <i>Nanoscale</i> , 2011, 3, 1171.	2.8	21
47	Nanoscale electrical and structural modification induced by rapid thermal oxidation of AlGaN/GaN heterostructures. <i>Nanotechnology</i> , 2014, 25, 025201.	1.3	21
48	High permittivity cerium oxide thin films on AlGaN/GaN heterostructures. <i>Applied Physics Letters</i> , 2013, 103, .	1.5	20
49	Effects of interface states and near interface traps on the threshold voltage stability of GaN and SiC transistors employing SiO ₂ as gate dielectric. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2017, 35, .	0.6	19
50	Identification of two trapping mechanisms responsible of the threshold voltage variation in SiO ₂ /4H-SiC MOSFETs. <i>Applied Physics Letters</i> , 2020, 117, .	1.5	19
51	A look underneath the SiO ₂ /4H-SiC interface after N ₂ O thermal treatments. <i>Beilstein Journal of Nanotechnology</i> , 2013, 4, 249-254.	1.5	18
52	Silicon nitride surfaces as active substrate for electrical DNA biosensors. <i>Sensors and Actuators B: Chemical</i> , 2017, 252, 492-502.	4.0	18
53	Understanding the role of threading dislocations on 4H-SiC MOSFET breakdown under high temperature reverse bias stress. <i>Nanotechnology</i> , 2020, 31, 125203.	1.3	18
54	Status and Prospects of Cubic Silicon Carbide Power Electronics Device Technology. <i>Materials</i> , 2021, 14, 5831.	1.3	18

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55	Theoretical Monte Carlo Study of the Formation and Evolution of Defects in the Homoepitaxial Growth of SiC. <i>Materials Science Forum</i> , 2008, 600-603, 135-138.	0.3	16
56	Raman probing of hydrogen-intercalated graphene on Si-face 4H-SiC. <i>Materials Science in Semiconductor Processing</i> , 2019, 96, 145-152.	1.9	16
57	Interfacial electrical and chemical properties of deposited SiO ₂ layers in lateral implanted 4H-SiC MOSFETs subjected to different nitridations. <i>Applied Surface Science</i> , 2021, 557, 149752.	3.1	16
58	Structural and Insulating Behaviour of High-Permittivity Binary Oxide Thin Films for Silicon Carbide and Gallium Nitride Electronic Devices. <i>Materials</i> , 2022, 15, 830.	1.3	16
59	Effects of high temperature annealing on MOCVD grown CaCu ₃ Ti ₄ O ₁₂ films on LaAlO ₃ substrates. <i>Surface and Coatings Technology</i> , 2007, 201, 9243-9247.	2.2	15
60	CaCu ₃ Ti ₄ O ₁₂ single crystals: insights on growth and nanoscopic investigation. <i>CrystEngComm</i> , 2011, 13, 3900.	1.3	15
61	Interface state density evaluation of high quality hetero-epitaxial 3C-SiC(001) for high-power MOSFET applications. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2015, 198, 14-19.	1.7	15
62	Laminated Al ₂ O ₃ /HfO ₂ layers grown by atomic layer deposition for microelectronics applications. <i>Thin Solid Films</i> , 2016, 601, 68-72.	0.8	15
63	Gold nanoparticle assisted synthesis of MoS ₂ monolayers by chemical vapor deposition. <i>Nanoscale Advances</i> , 2021, 3, 4826-4833.	2.2	15
64	Multiscale Investigation of the Structural, Electrical and Photoluminescence Properties of MoS ₂ Obtained by MoO ₃ Sulfurization. <i>Nanomaterials</i> , 2022, 12, 182.	1.9	15
65	Effect of SiO ₂ interlayer on the properties of Al ₂ O ₃ thin films grown by plasma enhanced atomic layer deposition on 4H-SiC substrates. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2017, 214, 1600365.	0.8	14
66	Barrier Inhomogeneity of Ni Schottky Contacts to Bulk GaN. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2018, 215, 1700613.	0.8	14
67	Impact of the Morphological and Electrical Properties of SiO ₂ /4H-SiC Interfaces on the Behavior of 4H-SiC MOSFETs. <i>ECS Journal of Solid State Science and Technology</i> , 2013, 2, N3006-N3011.	0.9	13
68	Nanoscale probing of the lateral homogeneity of donors concentration in nitridated SiO ₂ /4H-SiC interfaces. <i>Nanotechnology</i> , 2016, 27, 315701.	1.3	13
69	Nanolaminated Al ₂ O ₃ /HfO ₂ dielectrics for silicon carbide based devices. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2020, 38, .	0.9	13
70	Praseodymium based high-k dielectrics grown on Si and SiC substrates. <i>Materials Science in Semiconductor Processing</i> , 2006, 9, 1073-1078.	1.9	12
71	On the "Step Bunching" Phenomena Observed on Etched and Homoepitaxially Grown 4H Silicon Carbide. <i>Materials Science Forum</i> , 0, 679-680, 358-361.	0.3	12
72	An insight into the epitaxial nanostructures of NiO and CeO ₂ thin film dielectrics for AlGaN/GaN heterostructures. <i>Materials Chemistry and Physics</i> , 2015, 162, 461-468.	2.0	12

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73	Ni Schottky barrier on heavily doped phosphorous implanted 4H-SiC. Journal Physics D: Applied Physics, 2021, 54, 445107.	1.3	12
74	Effects of deposition temperature on the microstructural and electrical properties of praseodymium oxide-based films. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2005, 118, 117-121.	1.7	11
75	Nanoscale probing of dielectric breakdown at SiO ₂ /3C-SiC interfaces. Journal of Applied Physics, 2011, 109, .	1.1	11
76	Determining oxide trapped charges in Al ₂ O ₃ insulating films on recessed AlGaIn/GaN heterostructures by gate capacitance transients measurements. Japanese Journal of Applied Physics, 2018, 57, 050307.	0.8	11
77	Forward and reverse current transport mechanisms in tungsten carbide Schottky contacts on AlGaIn/GaN heterostructures. Journal of Applied Physics, 2021, 129, .	1.1	11
78	Correlating electron trapping and structural defects in Al ₂ O ₃ thin films deposited by plasma enhanced atomic layer deposition. AIP Advances, 2020, 10, .	0.6	11
79	Characterization of SiO ₂ /SiC Interfaces Annealed in N ₂ O or POCl ₃ . Materials Science Forum, 0, 778-780, 623-626.	0.3	10
80	Properties of Al ₂ O ₃ thin films deposited on 4H-SiC by reactive ion sputtering. Materials Science in Semiconductor Processing, 2019, 93, 290-294.	1.9	10
81	On the origin of the premature breakdown of thermal oxide on 3C-SiC probed by electrical scanning probe microscopy. Applied Surface Science, 2020, 526, 146656.	3.1	10
82	Breakdown kinetics at nanometer scale of innovative MOS devices by conductive atomic force microscopy. Microelectronic Engineering, 2007, 84, 441-445.	1.1	9
83	Early Growth Stages of Aluminum Oxide (Al ₂ O ₃) Insulating Layers by Thermal- and Plasma-Enhanced Atomic Layer Deposition on AlGaIn/GaN Heterostructures. ACS Applied Electronic Materials, 2022, 4, 406-415.	2.0	9
84	Template-Free and Seedless Growth of Pt Nanocolumns: Imaging and Probing Their Nanoelectrical Properties. ACS Nano, 2007, 1, 183-190.	7.3	8
85	Study of the Effects of Growth Rate, Miscut Direction and Postgrowth Argon Annealing on the Surface Morphology of Homoepitaxially Grown 4H Silicon Carbide Films. Materials Science Forum, 0, 740-742, 229-234.	0.3	8
86	Surface treatments on AlGaIn/GaN heterostructures for gate dielectric Al ₂ O ₃ thin films grown by Atomic Layer Deposition. Thin Solid Films, 2016, 617, 138-142.	0.8	8
87	Effects of Thermal Annealing Processes in Phosphorous Implanted 4H-SiC Layers. Materials Science Forum, 0, 963, 407-411.	0.3	8
88	Active dopant profiling and Ohmic contacts behavior in degenerate n-type implanted silicon carbide. Applied Physics Letters, 2020, 117, .	1.5	8
89	High-Resolution Two-Dimensional Imaging of the 4H-SiC MOSFET Channel by Scanning Capacitance Microscopy. Nanomaterials, 2021, 11, 1626.	1.9	8
90	Scanning Probe Microscopy on heterogeneous CaCu ₃ Ti ₄ O ₁₂ thin films. Nanoscale Research Letters, 2011, 6, 118.	3.1	7

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91	Nanoscale characterization of electrical transport at metal/3C-SiC interfaces. Nanoscale Research Letters, 2011, 6, 120.	3.1	7
92	Processing Issues in SiC and GaN Power Devices Technology: The Cases of 4H-SiC Planar MOSFET and Recessed Hybrid GaN MISHEMT. , 2018, , .		7
93	Conductive Atomic Force Microscopy Studies on the Reliability of Thermally Oxidized SiO ₂ /4H-SiC. Materials Science Forum, 2007, 556-557, 501-504.	0.3	6
94	Effects of surface nature of different semiconductor substrates on the plasma enhanced atomic layer deposition growth of Al ₂ O ₃ gate dielectric thin films. Physica Status Solidi C: Current Topics in Solid State Physics, 2015, 12, 980-984.	0.8	6
95	Industrial Approach for Next Generation of Power Devices Based on 4H-SiC. Materials Science Forum, 0, 821-823, 660-666.	0.3	6
96	Plasma enhanced atomic layer deposition of Al ₂ O ₃ gate dielectric thin films on AlGaIn/GaN substrates: The role of surface predeposition treatments. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2017, 35, 01B140.	0.9	6
97	Growth of 4H-SiC Epitaxial Layer through Optimization of Buffer Layer. Materials Science Forum, 0, 924, 84-87.	0.3	6
98	Highly Homogeneous Current Transport in Ultra-Thin Aluminum Nitride (AlN) Epitaxial Films on Gallium Nitride (GaN) Deposited by Plasma Enhanced Atomic Layer Deposition. Nanomaterials, 2021, 11, 3316.	1.9	6
99	3C-SiC Heteroepitaxy on (100), (111) and (110) Si Using Trichlorosilane (TCS) as the Silicon Precursor.. Materials Science Forum, 0, 600-603, 243-246.	0.3	5
100	Electrical properties of SiO ₂ /SiC interfaces on 2°-off axis 4H-SiC epilayers. Applied Surface Science, 2016, 364, 892-895.	3.1	5
101	WInSiC4AP: Wide Band Gap Innovative SiC for Advanced Power. , 2019, , .		5
102	Electrical characterization of trapping phenomena at SiO ₂ /SiC and SiO ₂ /GaN in MOS-based devices. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1600366.	0.8	5
103	Carrier Transport in Advanced Semiconductor Materials. , 2008, , 63-103.		5
104	CaCu ₃ Ti ₄ O ₁₂ thin films on conductive oxide electrode: A comparative study between chemical and physical vapor deposition routes. Materials Chemistry and Physics, 2012, 133, 1108-1115.	2.0	4
105	Binary and complex oxide thin films for microelectronic applications: An insight into their growth and advanced nanoscopic investigation. Surface and Coatings Technology, 2013, 230, 152-162.	2.2	4
106	Nanoscale Characterization of SiC Interfaces and Devices. Materials Science Forum, 0, 778-780, 407-413.	0.3	4
107	Oxide Traps Probed by Transient Capacitance Measurements on Lateral SiO ₂ /4H-SiC MOSFETs. Materials Science Forum, 0, 924, 285-288.	0.3	4
108	Defects induced anomalous breakdown kinetics in Pr ₂ O ₃ by micro- and nano-characterization. Microelectronics Reliability, 2007, 47, 640-644.	0.9	3

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109	Effects of a Post-Oxidation Annealing in Nitrous Oxide on the Morphological and Electrical Properties of SiO ₂ /4H-SiC Interfaces. Materials Science Forum, 2013, 740-742, 719-722.	0.3	3
110	Effects of the Growth Rate on the Quality of 4H Silicon Carbide Films for MOSFET Applications. Materials Science Forum, 0, 778-780, 95-98.	0.3	3
111	Electrical Properties Evaluation on High Quality Hetero-Epitaxial 3C-SiC(001) for MOSFET Applications. Materials Science Forum, 2015, 821-823, 773-776.	0.3	3
112	Correlation between MOSFETs breakdown and 4H-SiC epitaxial defects. , 2021, , .		3
113	Temperature and time dependent electron trapping in Al ₂ O ₃ thin films onto AlGaIn/GaN heterostructures. Applied Surface Science, 2022, 579, 152136.	3.1	3
114	Nanoscale Imaging of CaCu ₃ Ti ₄ O ₁₂ Dielectric Properties: The Role of Surface Defects. Solid State Phenomena, 2008, 131-133, 443-448.	0.3	2
115	Growth of 3C-SiC on Si: Influence of Process Pressure. Materials Science Forum, 0, 600-603, 211-214.	0.3	2
116	CaCu ₃ Ti ₄ O ₁₂ Thin Films for Capacitive Applications: MOCVD Synthesis and Nanoscopic/microscopic Characterization. ECS Transactions, 2009, 25, 135-142.	0.3	2
117	Detection of heterogeneities in single-crystal CaCu ₃ Ti ₄ O ₁₂ using conductive atomic force microscopy. IOP Conference Series: Materials Science and Engineering, 2010, 8, 012018.	0.3	2
118	Impact of Morphological Features on the Dielectric Breakdown at SiO ₂ /3C-SiC Interfaces. AIP Conference Proceedings, 2010, , .	0.3	2
119	Study of the Impact of Growth and Post-Growth Processes on the Surface Morphology of 4H Silicon Carbide Films. Materials Science Forum, 2012, 717-720, 149-152.	0.3	2
120	Nanoscale Probing of Interfaces in GaN for Devices Applications. ECS Transactions, 2013, 50, 439-446.	0.3	2
121	Impact of Substrate Steps and of Monolayer-Bilayer Junctions on the Electronic Transport in Epitaxial Graphene on 4H-SiC (0001). Materials Science Forum, 2013, 740-742, 113-116.	0.3	2
122	Potentialities of Nickel Oxide as Dielectric for GaN and SiC Devices. Materials Science Forum, 2013, 740-742, 777-780.	0.3	2
123	Voids-Free 3C-SiC/Si Interface for High Quality Epitaxial Layer. Materials Science Forum, 2016, 858, 159-162.	0.3	2
124	Hydrogen Flux Influence on Homo-Epitaxial 4H-SiC Doping Concentration Profile for High Power Application. Materials Science Forum, 2016, 858, 197-200.	0.3	2
125	X-Ray Irradiation on 4H-SiC MOS Capacitors Processed under Different Annealing Conditions. Materials Science Forum, 2016, 858, 659-662.	0.3	2
126	Impact of Phosphorus Implantation on the Electrical Properties of SiO ₂ /4H-SiC Interfaces Annealed in N ₂ O. Materials Science Forum, 2016, 858, 701-704.	0.3	2

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127	Atomic Layer Deposition of Al ₂ O ₃ Thin Films for Metal Insulator Semiconductor Applications on 4H-SiC. Materials Science Forum, 2016, 858, 685-688.	0.3	2
128	Properties of SiO ₂ /4H-SiC Interfaces with an Oxide Deposited by a High-Temperature Process. Materials Science Forum, 2017, 897, 331-334.	0.3	2
129	Fabrication and Characterization of Ohmic Contacts to 3C-SiC Layers Grown on Silicon. Materials Science Forum, 0, 963, 485-489.	0.3	2
130	Electrical Properties of Thermal Oxide on 3C-SiC Layers Grown on Silicon. Materials Science Forum, 2019, 963, 479-482.	0.3	2
131	Nanoscale Insights on the Origin of the Power MOSFETs Breakdown after Extremely Long High Temperature Reverse Bias Stress. Materials Science Forum, 0, 1004, 433-438.	0.3	2
132	Identification of Interface States responsible for V _{TH} Hysteresis in packaged SiC MOSFETs. , 2022, , .		2
133	Probing dielectric ceramics surface at sub-micrometer scale. IOP Conference Series: Materials Science and Engineering, 2010, 8, 012038.	0.3	1
134	Reliability of Thin Thermally Grown SiO ₂ on 3C-SiC Studied by Scanning Probe Microscopy. Materials Science Forum, 0, 645-648, 833-836.	0.3	1
135	A Nanoscale Look in the Channel of 4H-SiC Lateral MOSFETs. Materials Science Forum, 0, 740-742, 699-702.	0.3	1
136	Effects of a Post-Oxidation Annealing in Nitrous Oxide on the Morphological and Electrical Properties of SiO ₂ /4H-SiC Interfaces. Materials Science Forum, 0, 740-742, 715-718.	0.3	1
137	Scanning probe microscopy investigation of the mechanisms limiting electronic transport in substrate-supported graphene. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1188-1192.	0.8	1
138	Thermal and plasma-enhanced atomic layer deposition of hafnium oxide on semiconductor substrates. , 2014, , .		1
139	Origin of the Current Transport Anisotropy in Epitaxial Graphene Grown on Vicinal 4H-SiC (0001) Surfaces. Materials Science Forum, 0, 806, 103-107.	0.3	1
140	Epitaxial Growth on 150 mm 2° off Wafers. Materials Science Forum, 2015, 821-823, 157-160.	0.3	1
141	Temperature-Dependence Study of the Gate Current SiO ₂ /4H-SiC MOS Capacitors. Materials Science Forum, 0, 924, 473-476.	0.3	1
142	SiO ₂ /4H-SiC interfacial chemistry as origin of the threshold voltage instability in power MOSFETs. , 2022, , .		1
143	Current Transport by Defects in Pr ₂ O ₃ High K Films. Solid State Phenomena, 2005, 108-109, 717-722.	0.3	0
144	Electron Transport and Dielectric Breakdown Kinetics in Pr ₂ O ₃ High K Films. Advances in Science and Technology, 2006, 46, 21.	0.2	0

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145	New method for the detection of enzyme immobilized on Si-based glucose Biosensors. , 2006, , .		0
146	CaCu ₃ Ti ₄ O ₁₂ , a Novel Material for Capacitive Applications: Thin Film Growth and Characterization. ECS Transactions, 2007, 6, 385-395.	0.3	0
147	Conductive Atomic Force Microscopy and Scanning Impedance Microscopy for the Imaging of Electrical Domain in CaCu ₃ Ti ₄ O ₁₂ Perovskite Oxide. Materials Research Society Symposia Proceedings, 2009, 1232, 70101.	0.1	0
148	Probing heterogeneity in ptcr-BaTiO ₃ thermistors by local probe electrical measurements. IOP Conference Series: Materials Science and Engineering, 2010, 8, 012037.	0.3	0
149	Nanoscale reliability aspects of insulator onto wide band gap compounds. , 2014, , .		0
150	Probing at Nanoscale Underneath the Gate Oxides in 4H-SiC MOS-Based Devices Annealed in N ₂ and POCl ₃ . Materials Science Forum, 0, 806, 143-147.	0.3	0
151	Processing and Characterization of MOS Capacitors Fabricated on 2°-Off Axis 4H-SiC Epilayers. Materials Science Forum, 0, 858, 663-666.	0.3	0
152	Conduction Mechanisms at SiO ₂ /4H-SiC Interfaces in MOS-Based Devices Subjected to Post Deposition Annealing in N ₂ O. Materials Science Forum, 2016, 858, 705-708.	0.3	0
153	Trapping States in SiO ₂ /GaN MOS Capacitors Fabricated on Recessed AlGaIn/GaN Heterostructures. Materials Science Forum, 2016, 858, 1178-1181.	0.3	0
154	Anomalous Fowler-Nordheim Tunneling through SiO ₂ /4H-SiC Barrier Investigated by Temperature and Time Dependent Gate Current Measurements. Materials Science Forum, 0, 897, 123-126.	0.3	0
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